

What is claimed is:

1. A method for fabricating a contact pad of a semiconductor device, the method comprising:
 - forming a plurality of conductive layer patterns displaced on a silicon substrate with adjoining to each other;
 - forming an insulating layer on a top of the conductive layer patterns;
 - depositing a material layer serving as a hard mask on the insulating layer;
 - forming a photoresist pattern between the conductive layer patterns on the hard mask material layer to form a contact hole;
 - defining an area for forming a contact by forming by etching the hard mask material layer with utilizing the photoresist pattern as an etching mask;
 - removing the photoresist pattern;
 - exposing the silicon substrate by etching the insulating layer with utilizing the hard mask as an etching mask to thereby form an open portion;
 - forming a polymer layer on the open portion;
 - exposing the silicon substrate by removing the hard mask and the polymer layer by implementing an etch back process; and
 - forming a contacted pad on the exposed silicon substrate.
2. The method of claim 1, wherein the conductive layer pattern includes any one of a gate electrode pattern, a bit line pattern or a metal wiring.
3. The method of claim 1, wherein, in the step of forming the photoresist pattern comprises using an argon fluoride (ArF) photoresist and an ArF light source.
4. The method of claim 1, wherein the hard mask material layer includes an insulating material layer selected from the group consisting of a SiC layer, an undoped poly silicon layer, a silicon nitride layer, and a silicon oxide nitride layer.
5. The method of claim 1, wherein the insulating material layer is formed at a thickness ranging of about 400 Å to about 2000 Å.

6. The method of claim 1, wherein the hard mask material layer includes a conductive material layer selected from the group consisting of a tungsten layer, a tungsten silicide layer or a doped poly silicon layer.

5 7. The method of claim 1, further comprising the step of forming a bottom arc layer with an organic material.

8. The method of claim 1, wherein the contact pad is a doped poly silicon layer.

10

9. A semiconductor device made in accordance with the method of claim 1.

10. A semiconductor device made in accordance with the method of claim 15 2.

11. A semiconductor device made in accordance with the method of claim 3.

12. A semiconductor device made in accordance with the method of claim 20 4.

13. A semiconductor device made in accordance with the method of claim 25 5.

14. A semiconductor device made in accordance with the method of claim 6.

15. A semiconductor device made in accordance with the method of claim 30 7.

16. A semiconductor device made in accordance with the method of claim 8.